

# Energieforschung und Umsetzung

**Herausforderung in der**

**Technologie  
Akzeptanz  
Finanzierung**

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CEO Empa, CORE Mitglied**

# Gründe für Energieforschung und Umsetzung

- Langfristiges Erfüllen unserer Bedürfnisse für hohe Lebensqualität (Heizen, Kühlen, Mobilität, Transport, Maschinen, Geräte, Produktion)
- Nachhaltigkeit, Treibhausgase, Gesundheit
- Wirtschaftlich am Markt der Energietechnologie teilnehmen
- Innovative neue Produkte entwickeln
- Energietechnologie für Schwellenländer

# ENERGY RESOURCES

3000 B.C.

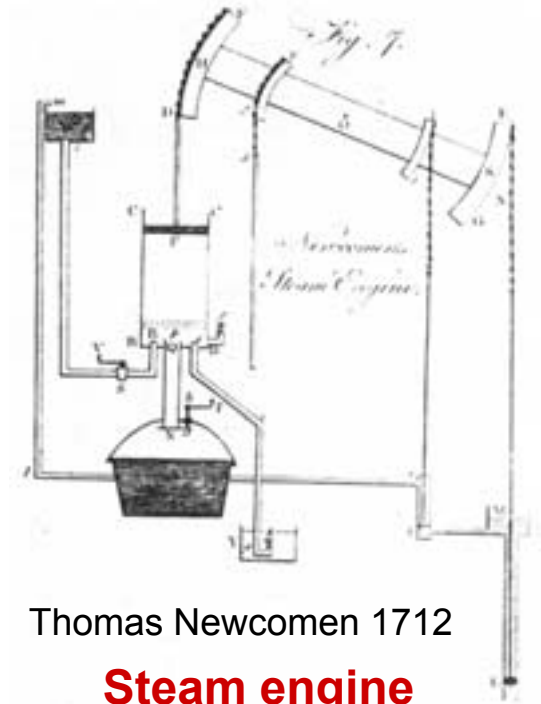


**Human power**  
(0.1 kW/person)

1000 B.C.



**Horse power**



Thomas Newcomen 1712

**Steam engine**

1700



**Carbon (C)**

Andreas Züttel, University of Fribourg, 15.12.2002

1800



**Oil (-CH<sub>2</sub>-)**

1900



**Natural gas (CH<sub>4</sub>)**

# ENERGY CONSUMPTION

Energy carrier	Demand	Reserve [years]
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## Fossile

Crude Oil	32.7 %	41
Natural Gas	19.5 %	63
Coal	21.4 %	218

## Renewable

Hydropower	6.7 %
Biomass	11.6 %
Others	2.0 %

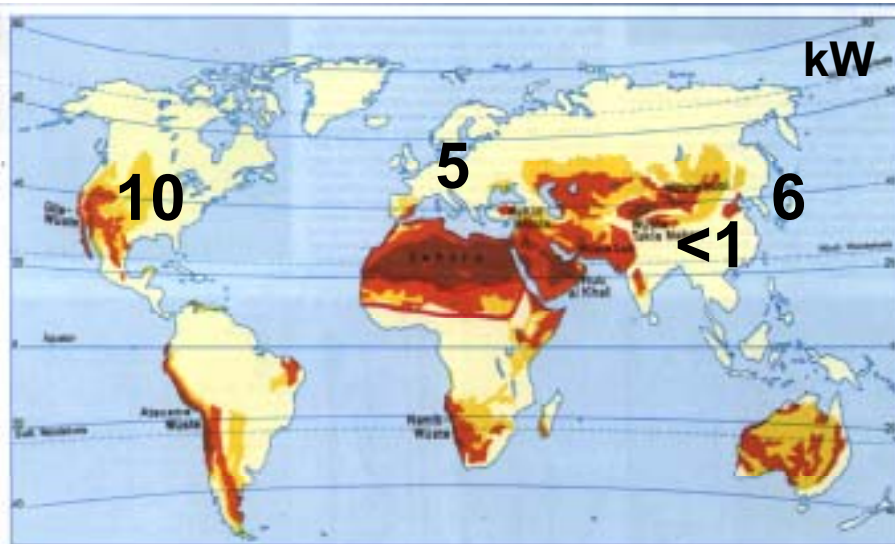
<b>Nuclear</b>	<b>6.1 %</b>	<b>100</b>
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20th Century



Average Power Consumption per Person

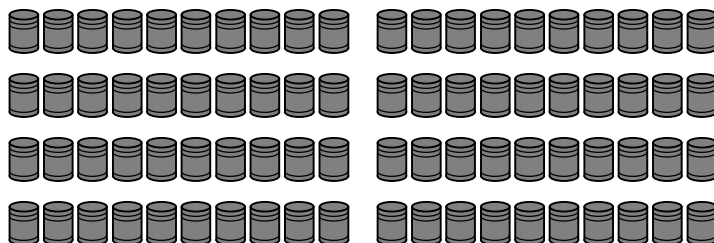


World = 2 kW/person for 2 Bil. = 0 kW

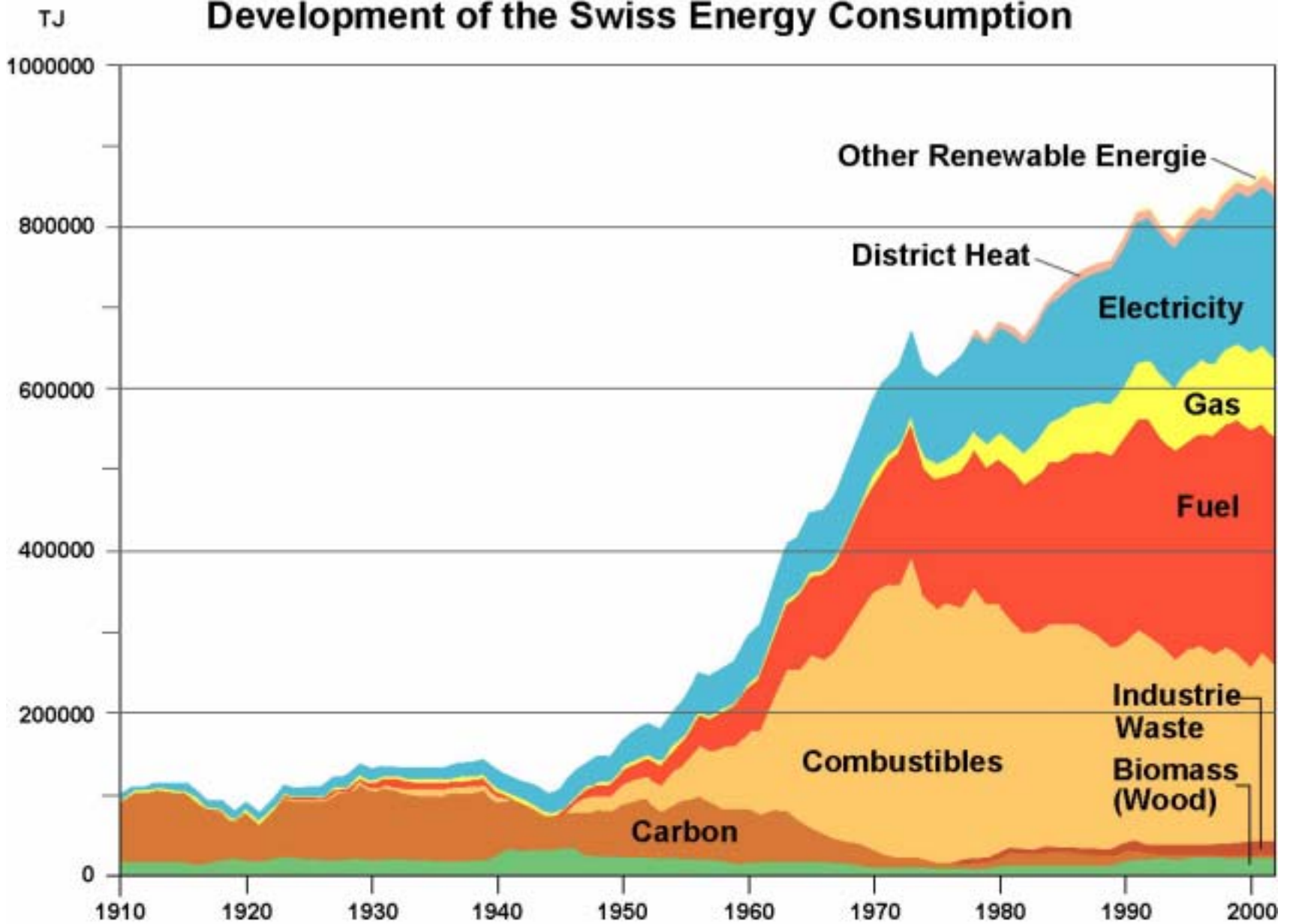
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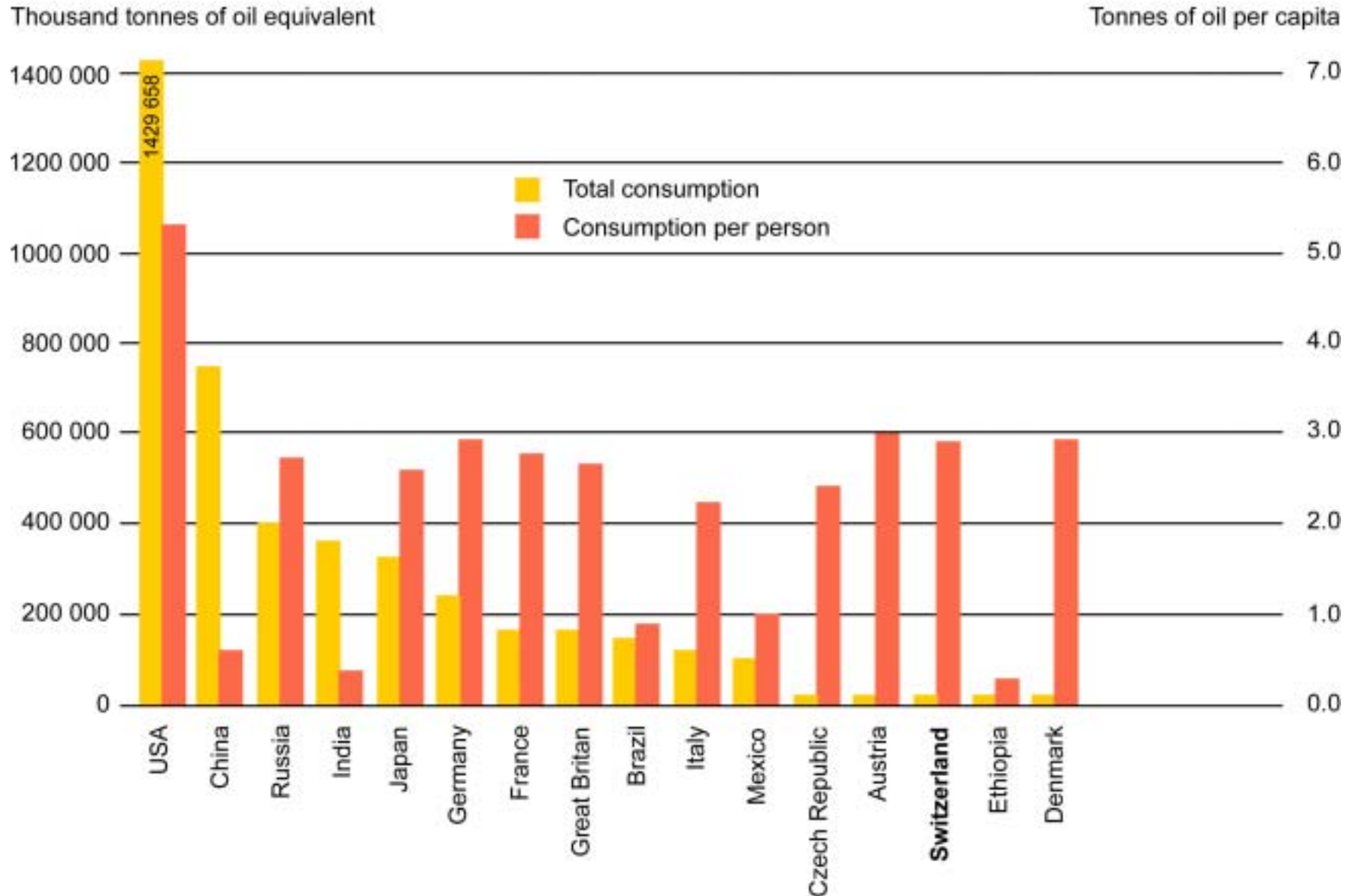
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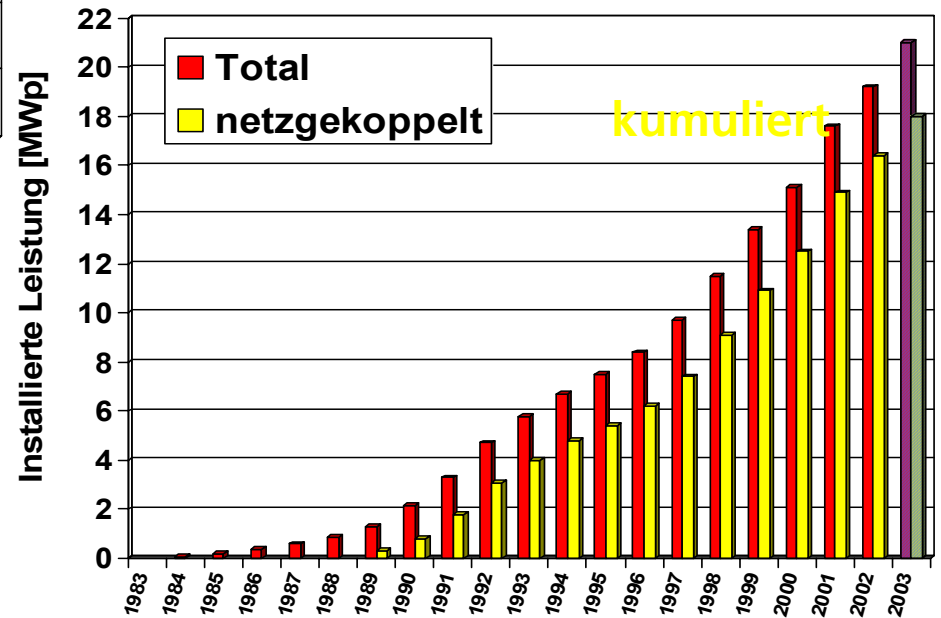
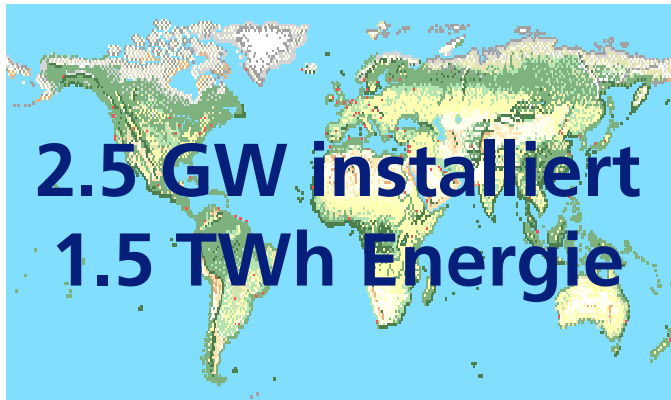
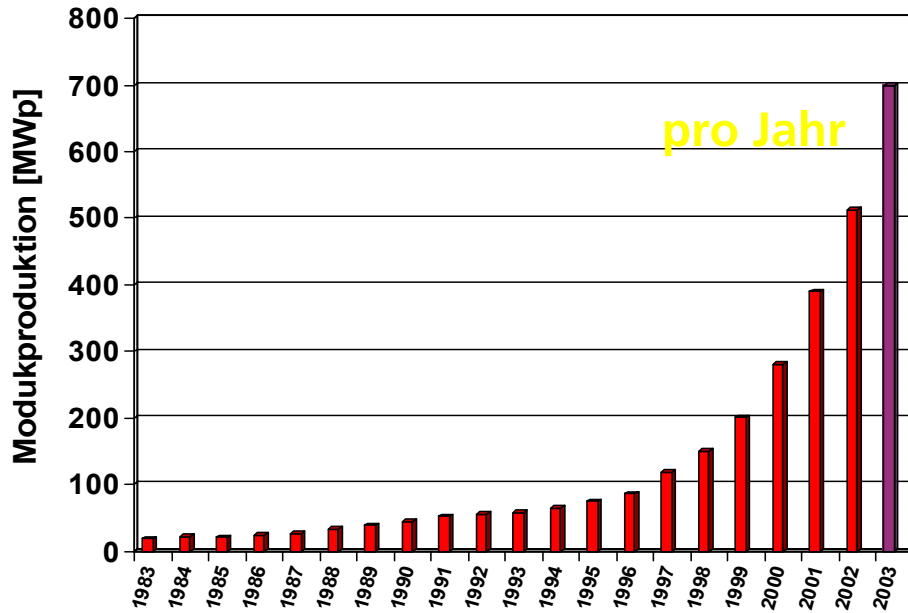
# Development of the Swiss Energy Consumption



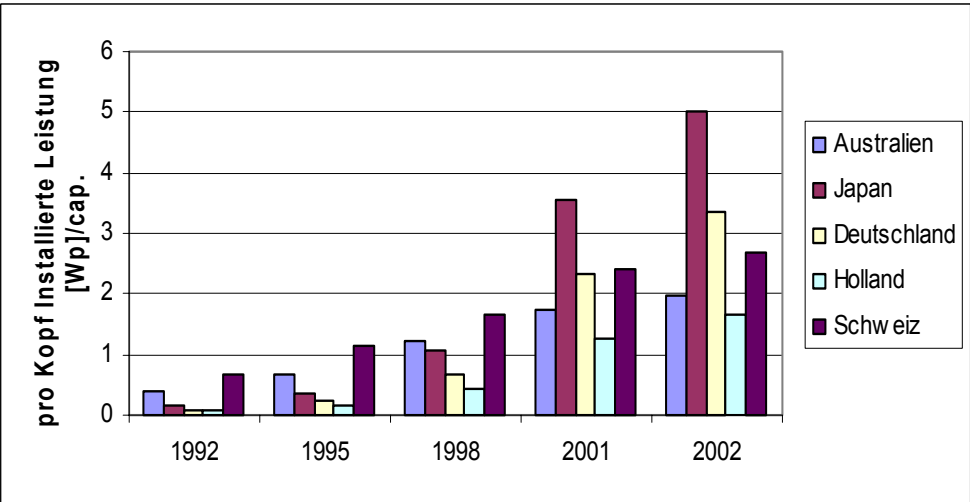
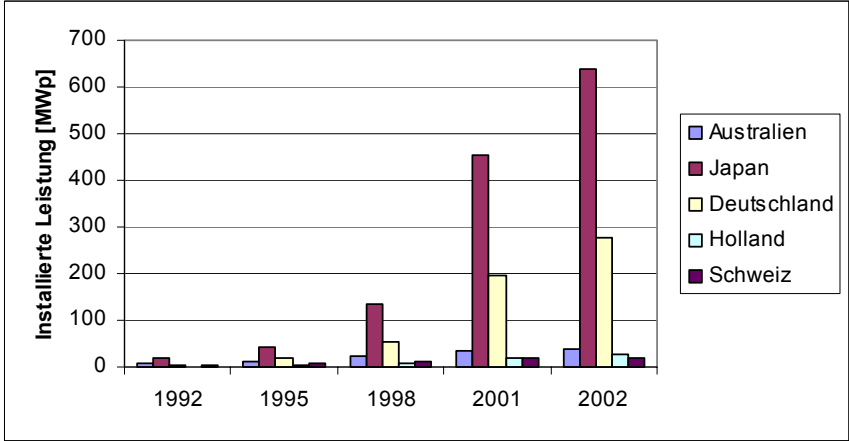
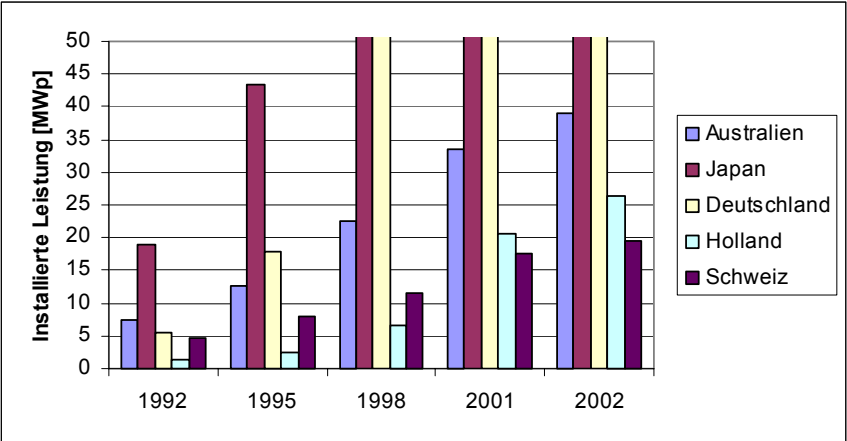
# International comparison of energy consumption 1998



# Der Photovoltaik Markt



# Vergleich total / per capita



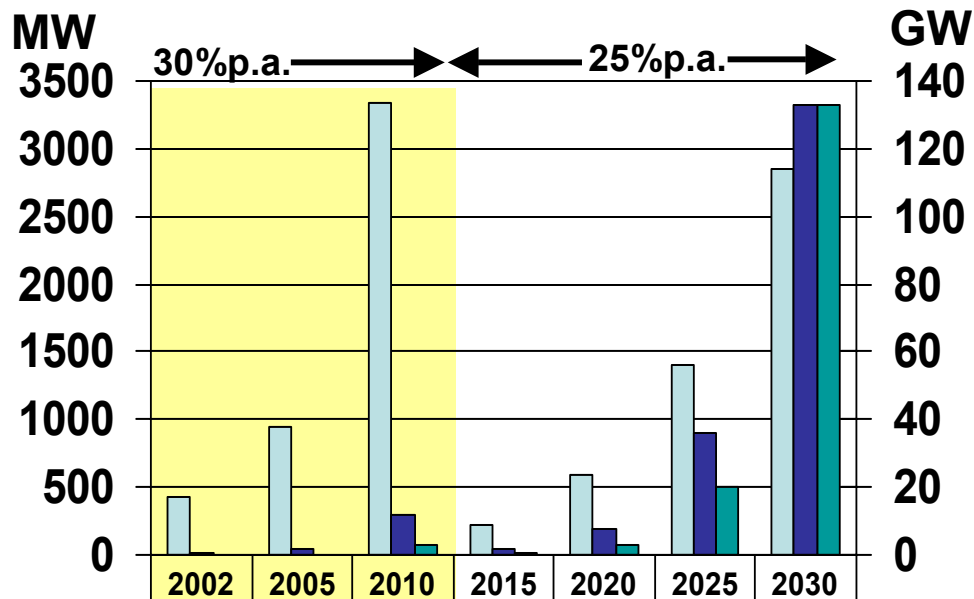
# The four main technology routes

<b>(a) Crystalline Silicon</b>		<b>(b) Thin Film</b>	
Cz, Fz	High power/area @ premium price eta 16 - 25 % space, niche markets	II - VI compound (CIS, CTS) a-Si / $\mu$ c-Si and thin Si films	Additional solutions for cost effective power applications eta 8 - 18 %
mc & ribbon (EFG)	Cost effective power application eta 14 - 16 % "The PV workhorse"	pin-ASI and ASI-THRU®	Low price/area @ low eta eta 4 - 6 % "Solar electricity glass"
<b>(c) III - V compounds (GaAs)</b>		<b>(d) New Concepts</b>	
"multi band gap" GaAs	Highest power/area @ very high price, eta 25 - 40 % space, concentrating systems	dye cells	"Colour to PV" (eta 3 - 10 %)
		organic cells	"low material cost option"
		Scientific high eta approaches aiming for eta 30 - 60 %	utilization of hot electrons, intermediate band cells, up/down conversion, quantum wells, nanostructures etc.

# Production of Solar Modules using different Technologies

## 2010 (Forecast)

Jp	1.200
EU	1.000
US	500
SOA	500
ROW	500
$\Sigma$	3.700




























	2002	2005	2010	2015	2020	2025	2030
c-Si	430	950	3340				
thin film	20	50	290				
"New Concepts"			70				
c-Si				8.96	23.8	56	114
thin film				1.68	7.48	36	133
"New Concepts"				0.56	2.72	20	133




c-Si
thin film
"New Concepts"



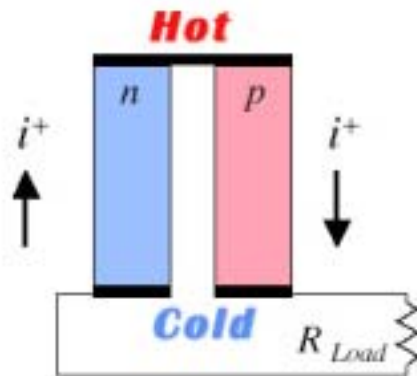
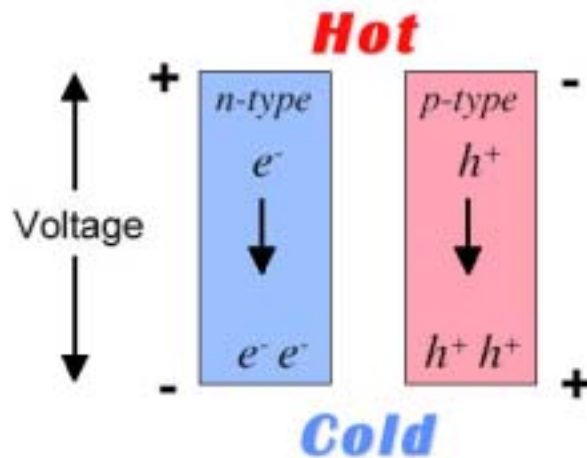
# Changing the Solar Paradigm

## Wireless distributed power becomes reality

Attributes			Thin Film 2 <sup>nd</sup> Gen	Crystalline 1 <sup>st</sup> Gen
Less than \$1 / watt	<b>Cost</b>			
Less than 50g / m <sup>2</sup>	<b>Weight</b>			
Tensile and modulus strength	<b>Flexibility</b>			
Size and Shape	<b>Form Factor</b>			
Reds, Yellows, Blues	<b>Colorable</b>			
85% transparent	<b>Transparent</b>			
Utility indoors	<b>Indoor</b>			
Theoretically 25%	<b>Efficiency</b>			

 **Significant Advantage**    
  **Moderate Advantage**    
  **Distinct Disadvantage**

# Thermopower



## Effect of Temp Gradient

Hot mobile species move faster

- $mv^2 = 3kT$
- Net diffusion to cold side

Establishes density gradient

- e.g. in a gas  $\rho = n/V = (P/R) / T$
- Cold = dense Hot = rarefied

Charge buildup on cold side

- Forces carriers back
- Produces Voltage
- +/- depends on sign of carrier

## Seebeck Voltage - Thermopower

$$V = \alpha \Delta T$$

- $-E = \nabla V = \alpha \nabla T$
- Seebeck Coefficient  $\alpha$
- Produces electricity from Heat

# The figure of merit $z$


$$z = \frac{\alpha^2 \cdot \sigma}{k}$$

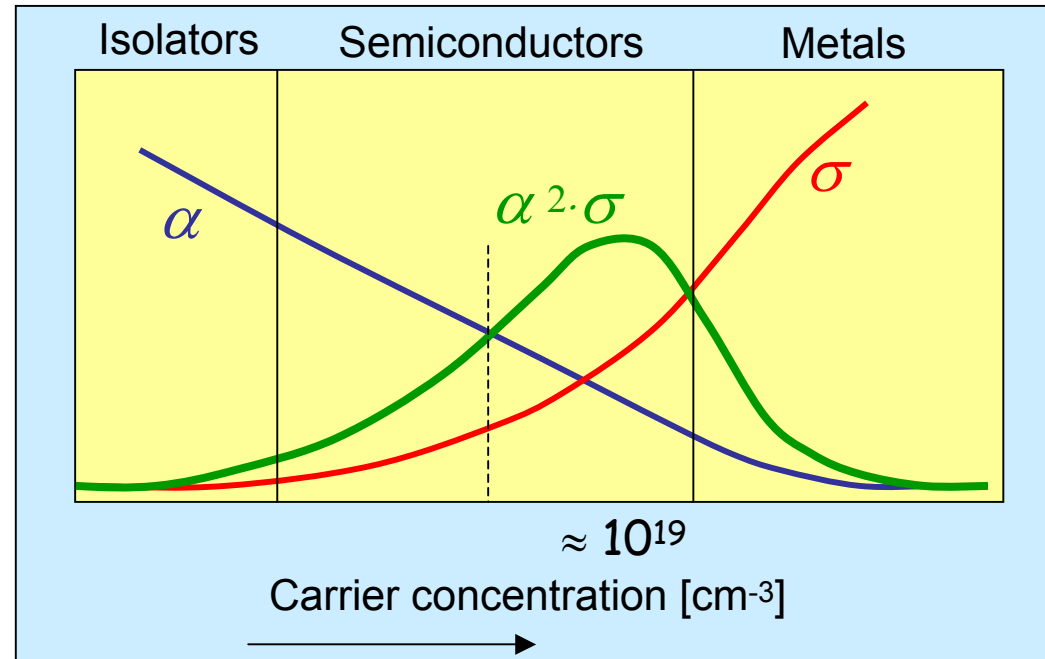
The efficiency  $h$  of a thermoelectric device is related to  $z$ .

- For maximum device efficiency one needs to **maximise**  $z$  :

Seebeck coefficient  $\alpha$  

Electrical conductivity  $\sigma$  

Thermal conductivity  $k$    
( $k = k_{lattice} + k_{electron}$ )



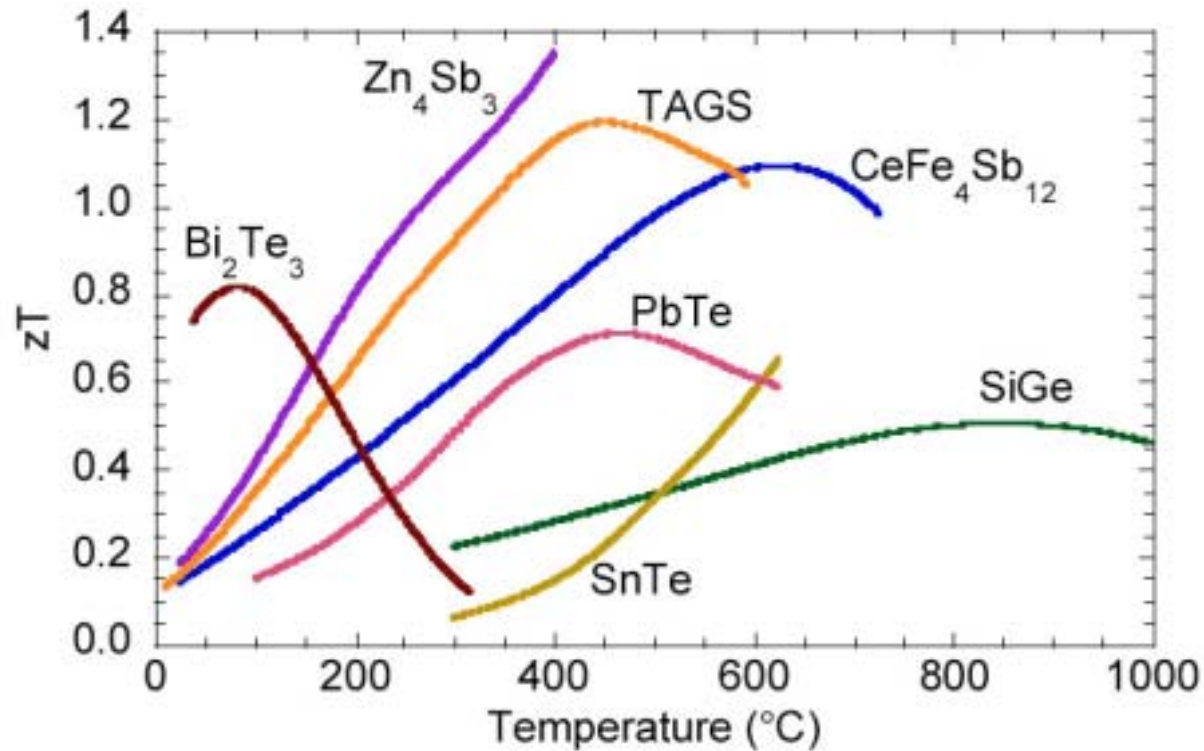
- Semiconductors with a carrier concentration of  $10^{19} \text{ cm}^{-3}$  satisfy the necessary criteria better than other materials .

# Advanced TE Materials



High zT materials

Do they have Electron Crystal - Phonon Glass properties?



# Improved Segmented TAGS

TAGS has high  $zT$  - stable to 525°C

**10.45%** efficiency

n-PbTe stable to 600°C

525°C to 600°C p-type segment needed

p-PbTe has highest  $zT$  (before skutterudites)

But not compatible ( $S_{PbTe} < 2 S_{TAGS}$ )

**10.33%** efficiency **decrease**

p-SnTe has low  $zT$ , and some compatibility

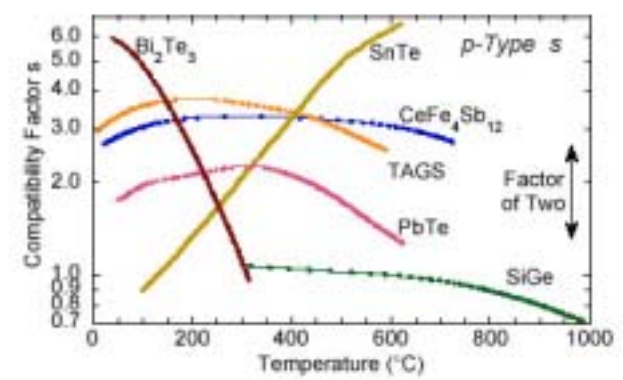
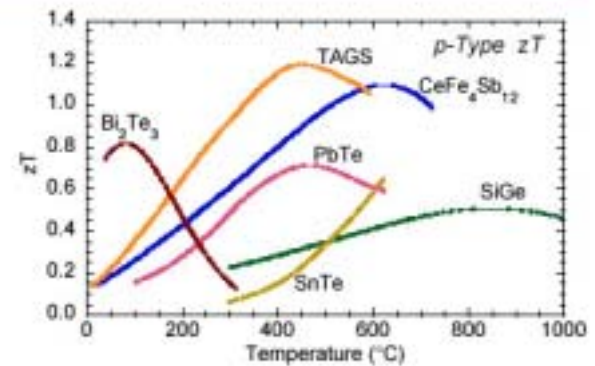
$S_{SnTe} \geq 2 S_{TAGS}$

**11.09%** small efficiency increase

p-Skutterudite has high  $zT$ , and compatibility

**11.87%** large efficiency increase

**13.56%** for 700°C hot side



Material	Efficiency (%)	$T_c$ (C)	$T_{interface}$ (C)	$T_h$ (C)	$u(T_c)$ (V <sup>2</sup> )
p-TAGS	10.45	100		525	2.97
p-TAGS/PbTe	10.33	100	525	600	2.33
p-TAGS/SnTe	11.09	100	525	600	2.84
p-TAGS/CeFe <sub>4</sub> Sb <sub>12</sub>	11.87	100	525	600	2.94
p-TAGS/CeFe <sub>4</sub> Sb <sub>12</sub>	13.56	100	525	700	2.88